



6-Pin DIP Optoisolators Transistor Output

The H11AV1,A and H11AV2,A devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector.

- Guaranteed 70 Volt $V_{(BR)CEO}$ Minimum
- 'A' Suffix = 0.400" Wide Spaced Leadform (Same as 'T' Suffix.)
- *To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.*

Applications

- General Purpose Switching Circuits
- Interfacing and coupling systems of different potentials and impedances
- Monitor and Detection Circuits
- Regulation and Feedback Circuits
- Solid State Relays

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
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INPUT LED

Reverse Voltage	V_R	6	Volts
Forward Current — Continuous	I_F	60	mA
LED Power Dissipation @ $T_A = 25^\circ\text{C}$ with Negligible Power in Output Detector Derate above 25°C	P_D	120 1.41	mW mW/ $^\circ\text{C}$

OUTPUT TRANSISTOR

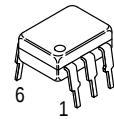
Collector–Emitter Voltage	V_{CEO}	70	Volts
Emitter–Base Voltage	V_{EBO}	7	Volts
Collector–Base Voltage	V_{CBO}	70	Volts
Collector Current — Continuous	I_C	150	mA
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ with Negligible Power in Input LED Derate above 25°C	P_D	150 1.76	mW mW/ $^\circ\text{C}$

TOTAL DEVICE

Isolation Surge Voltage ⁽¹⁾ (Peak ac Voltage, 60 Hz, 1 sec Duration)	V_{ISO}	7500	Vac(pk)
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	250 2.94	mW mW/ $^\circ\text{C}$
Ambient Operating Temperature Range	T_A	–55 to +100	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	–55 to +150	$^\circ\text{C}$
Soldering Temperature (10 sec, 1/16" from case)	T_L	260	$^\circ\text{C}$

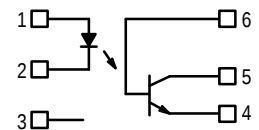
1. Isolation surge voltage is an internal device dielectric breakdown rating.
For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

H11AV1,A
H11AV2,A



STANDARD THRU HOLE

SCHEMATIC



- PIN 1. LED ANODE
2. LED CATHODE
3. N.C.
4. EMITTER
5. COLLECTOR
6. BASE

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)⁽¹⁾

Characteristic	Symbol	Min	Typ ⁽¹⁾	Max	Unit
INPUT LED					
Forward Voltage ($I_F = 10\text{ mA}$)	V_F	0.8 0.9 0.7	1.15 1.3 1.05	1.5 1.7 1.4	Volts
Reverse Leakage Current ($V_R = 6\text{ V}$)	I_R	—	—	10	μA
Capacitance ($V = 0\text{ V}$, $f = 1\text{ MHz}$)	C_J	—	18	—	pF

OUTPUT TRANSISTOR

Collector–Emitter Dark Current ($V_{CE} = 10\text{ V}$)	I_{CEO}	—	5	50	nA
Collector–Base Dark Current ($V_{CB} = 10\text{ V}$)	I_{CBO}	—	0.5	—	nA
Collector–Emitter Breakdown Voltage ($I_C = 1\text{ mA}$)	$V_{(BR)CEO}$	70	100	—	Volts
Collector–Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$)	$V_{(BR)CBO}$	70	100	—	Volts
Emitter–Collector Breakdown Voltage ($I_E = 100\text{ }\mu\text{A}$)	$V_{(BR)ECO}$	7	8	—	Volts
DC Current Gain ($I_C = 2\text{ mA}$, $V_{CE} = 10\text{ V}$) (Typical Value)	h_{FE}	—	500	—	—
Collector–Emitter Capacitance ($f = 1\text{ MHz}$, $V_{CE} = 10\text{ V}$)	C_{CE}	—	4.5	—	pF

COUPLED

Output Collector Current ($I_F = 10\text{ mA}$, $V_{CE} = 10\text{ V}$) H11AV1, H11AV1A H11AV2, H11AV2A	I_C (CTR) ⁽²⁾	10 (100) 5 (50)	15 (150) 10 (100)	30 (300) —	mA (%)
Collector–Emitter Saturation Voltage ($I_C = 2\text{ mA}$, $I_F = 20\text{ mA}$)	$V_{CE(sat)}$	—	0.15	0.4	Volts
Turn–On Time ($I_C = 2\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾	t_{on}	—	5	15	μs
Turn–Off Time ($I_C = 2\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾	t_{off}	—	4	15	μs
Isolation Voltage ($f = 60\text{ Hz}$, $t = 1\text{ sec}$) ⁽⁴⁾	V_{ISO}	7500	—	—	Vac(pk)
Isolation Resistance ($V = 500\text{ V}$) ⁽⁴⁾	R_{ISO}	10^{11}	—	—	Ω
Isolation Capacitance ($V = 0\text{ V}$, $f = 1\text{ MHz}$) ⁽⁴⁾	C_{ISO}	—	0.2	0.5	pF

1. Always design to the specified minimum/maximum electrical limits (where applicable).

2. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

3. For test circuit setup and waveforms, refer to Figure 11.

4. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

TYPICAL CHARACTERISTICS

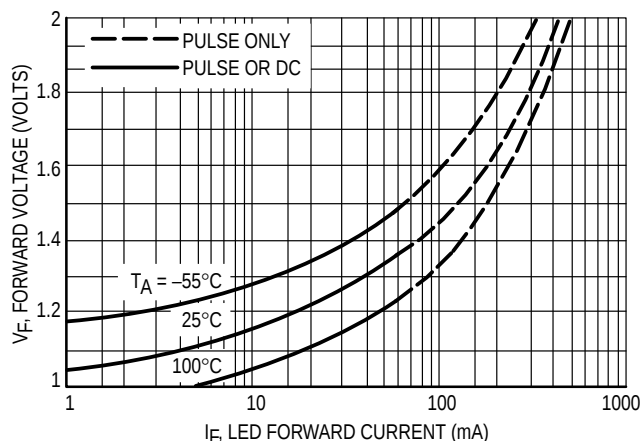


Figure 1. LED Forward Voltage versus Forward Current

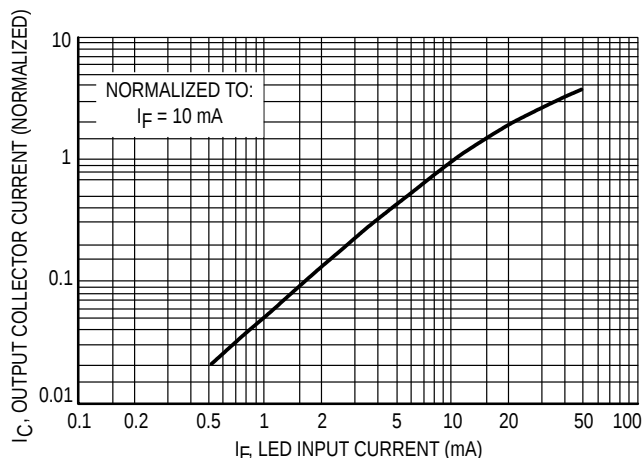


Figure 2. Output Current versus Input Current

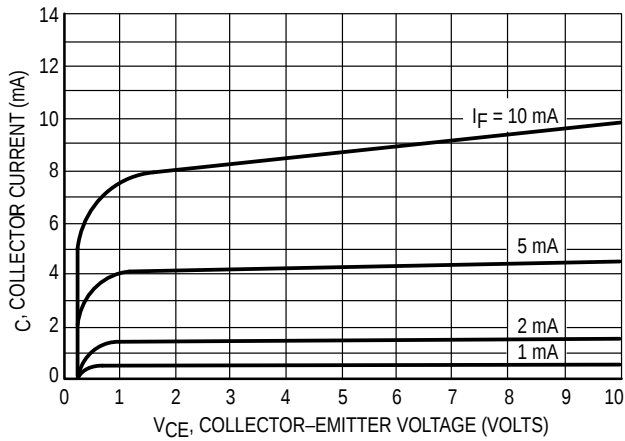


Figure 3. Collector Current versus Collector-Emitter Voltage

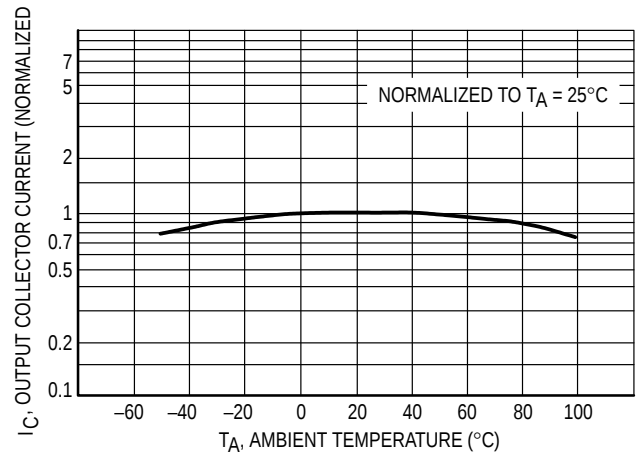


Figure 4. Output Current versus Ambient Temperature

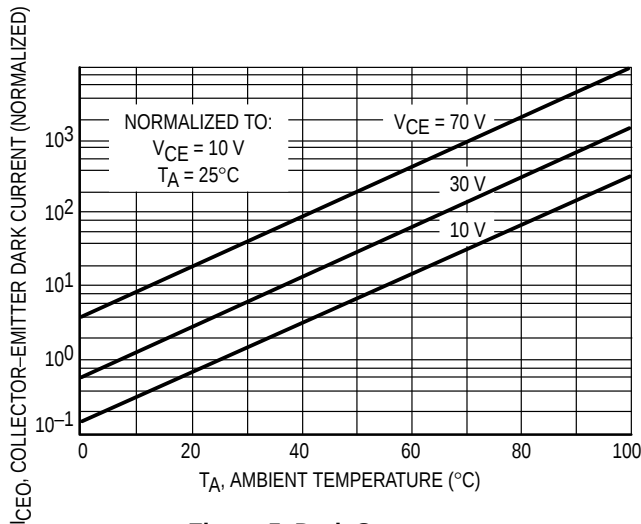


Figure 5. Dark Current versus Ambient Temperature

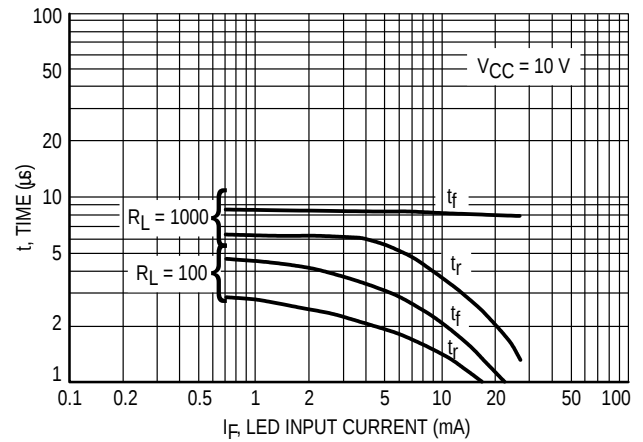


Figure 6. Rise and Fall Times (Typical Values)

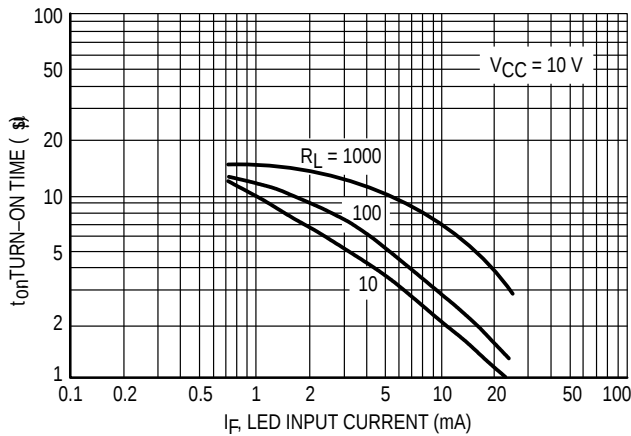


Figure 7. Turn-On Switching Times

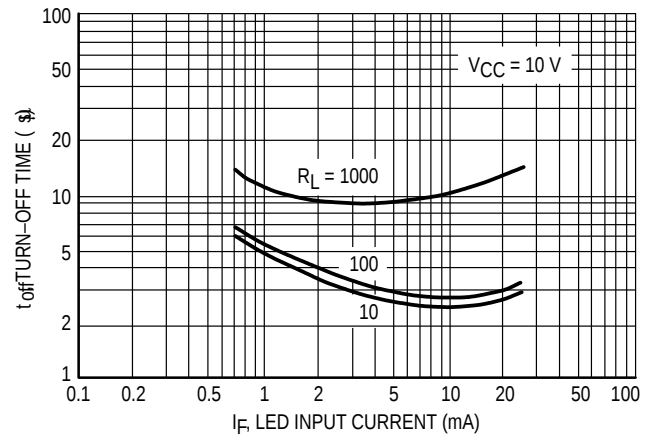


Figure 8. Turn-Off Switching Times

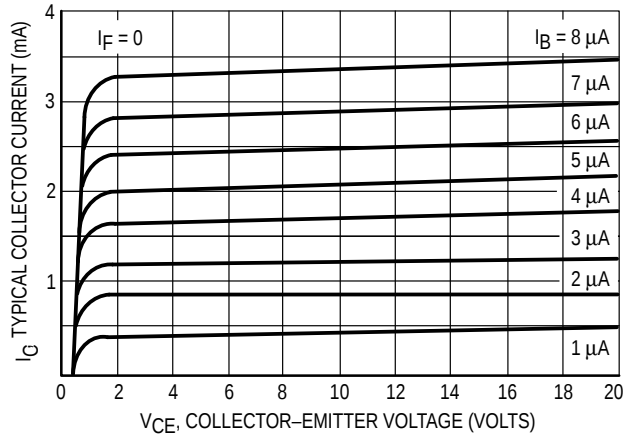


Figure 9. DC Current Gain (Detector Only)

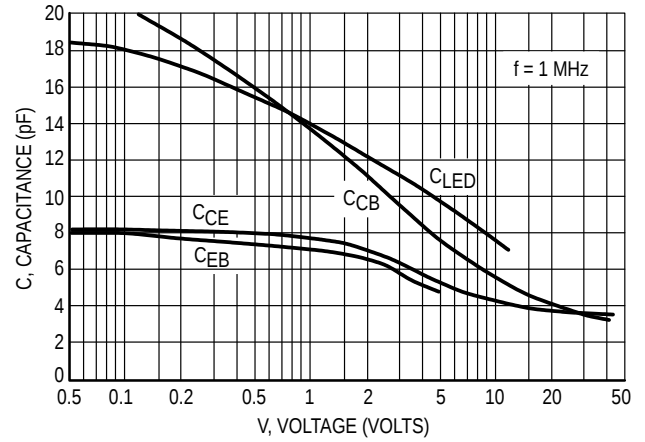


Figure 10. Capacitances versus Voltage

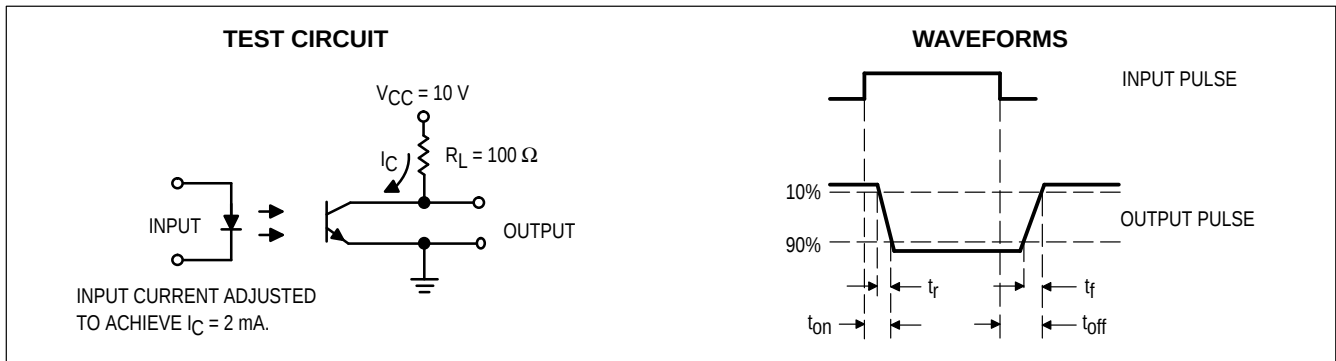
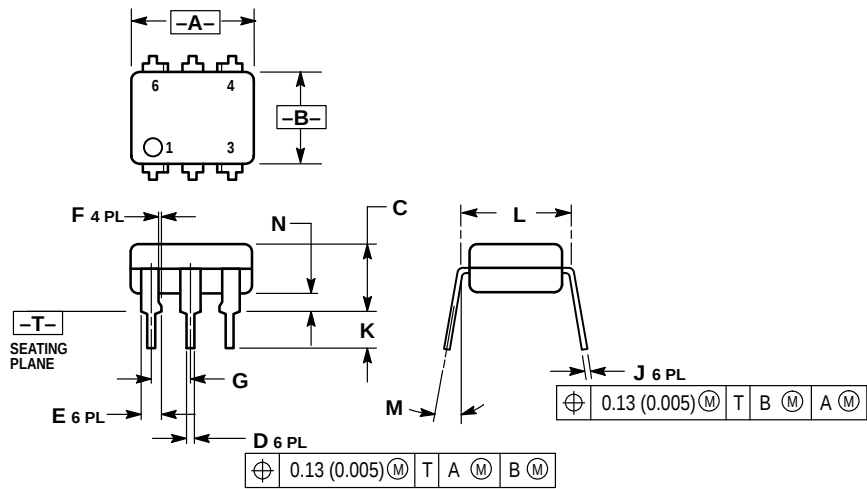


Figure 11. Switching Time Test Circuit and Waveforms

PACKAGE DIMENSIONS

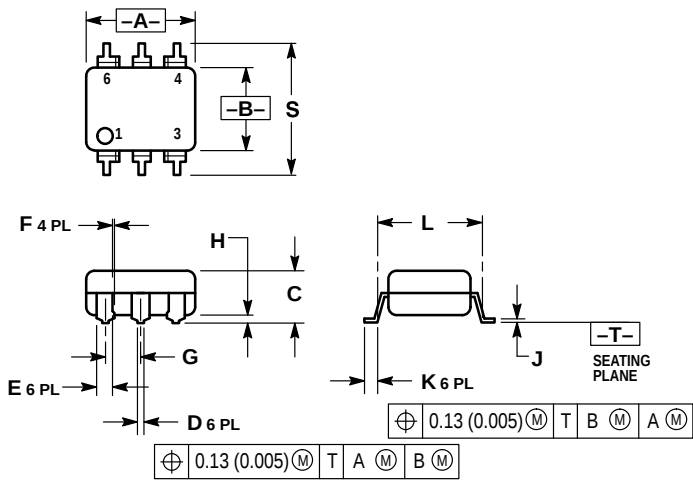


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.320	0.350	8.13	8.89
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.015	0.100	0.38	2.54

- STYLE 1:
- PIN 1. ANODE
 2. CATHODE
 3. NC
 4. EMITTER
 5. COLLECTOR
 6. BASE

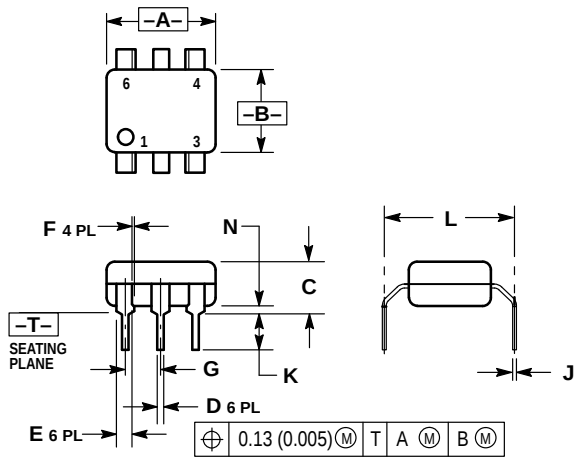
THRU HOLE



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DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.320	0.350	8.13	8.89
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
H	0.020	0.025	0.51	0.63
J	0.008	0.012	0.20	0.30
K	0.006	0.035	0.16	0.88
L	0.320 BSC		8.13 BSC	
S	0.332	0.390	8.43	9.90

SURFACE MOUNT



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0.4" LEAD SPACING

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